

Gaudenzio Meneghesso

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

562
papers

10,347
citations

48
h-index

79
g-index

627
ext. papers

12,424
ext. citations

2.4
avg, IF

6.13
L-index

#	Paper	IF	Citations
562	Laser-induced activation of Mg-doped GaN: quantitative characterization and analysis. <i>Journal Physics D: Applied Physics</i> , 2022 , 55, 185104	3	0
561	Photon-induced degradation of InGaN-based LED in open-circuit conditions investigated by steady-state phot capacitance and photoluminescence. <i>Journal of Applied Physics</i> , 2022 , 131, 043102	2.5	1
560	Trap-state mapping to model GaN transistors dynamic performance.. <i>Scientific Reports</i> , 2022 , 12, 1755	4.9	0
559	Origin of the Diffusion-Related Optical Degradation of 1.3 μm InAs QD-LDs Epitaxially Grown on Silicon Substrate. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2022 , 28, 1-9	3.8	0
558	Reliability of Commercial UVC LEDs: 2022 State-of-the-Art. <i>Electronics (Switzerland)</i> , 2022 , 11, 728	2.6	4
557	Study and characterization of GaN MOS capacitors: Planar vs trench topographies. <i>Applied Physics Letters</i> , 2022 , 120, 143501	3.4	1
556	Logarithmic trapping and detrapping in EGa ₂ O ₃ MOSFETs: Experimental analysis and modeling. <i>Applied Physics Letters</i> , 2022 , 120, 163502	3.4	
555	GaN-based power devices: Physics, reliability, and perspectives. <i>Journal of Applied Physics</i> , 2021 , 130, 181101	2.5	37
554	Understanding the effects of off-state and hard-switching stress in gallium nitride-based power transistors. <i>Semiconductor Science and Technology</i> , 2021 , 36, 014001	1.8	6
553	A Review of the Reliability of Integrated IR Laser Diodes for Silicon Photonics. <i>Electronics (Switzerland)</i> , 2021 , 10, 2734	2.6	1
552	Charge trapping in 0.1 μm AlGa _N /GaN RF HEMTs: Dependence on barrier properties, voltage and temperature. <i>Microelectronics Reliability</i> , 2021 , 126, 114259	1.2	
551	Degradation mechanisms of 1.3 μm C-doped quantum dot lasers grown on native substrate. <i>Microelectronics Reliability</i> , 2021 , 114222	1.2	0
550	Electrical, optical characterization and degradation of Cu(InGa)Se ₂ devices with fluorine-doped tin oxide back contact. <i>Microelectronics Reliability</i> , 2021 , 126, 114260	1.2	0
549	Non-monotonic threshold voltage variation in 4H-SiC metal oxide semiconductor field-effect transistor: Investigation and modeling. <i>Journal of Applied Physics</i> , 2021 , 130, 145702	2.5	1
548	Positive and negative charge trapping GaN HEMTs: Interplay between thermal emission and transport-limited processes. <i>Microelectronics Reliability</i> , 2021 , 114255	1.2	1
547	Impact of an AlGa _N spike in the buffer in 0.15 μm AlGa _N /GaN HEMTs during step stress. <i>Microelectronics Reliability</i> , 2021 , 126, 114318	1.2	1
546	Review on the degradation of GaN-based lateral power transistors. <i>E-Prime</i> , 2021 , 1, 100018		

545	Defect incorporation in In-containing layers and quantum wells: experimental analysis via deep level profiling and optical spectroscopy. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 025108	3	6
544	Understanding the Leakage Mechanisms and Breakdown Limits of Vertical GaN-on-Si pnn Diodes: The Road to Reliable Vertical MOSFETs. <i>Micromachines</i> , 2021 , 12,	3.3	5
543	Inactivating SARS-CoV-2 Using 275 nm UV-C LEDs through a Spherical Irradiation Box: Design, Characterization and Validation. <i>Materials</i> , 2021 , 14,	3.5	12
542	Challenges and Perspectives for Vertical GaN-on-Si Trench MOS Reliability: From Leakage Current Analysis to Gate Stack Optimization. <i>Materials</i> , 2021 , 14,	3.5	2
541	Influence of Carbon on pBTI Degradation in GaN-on-Si E-Mode MOSc-HEMT. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 2017-2024	2.9	1
540	. <i>IEEE Electron Device Letters</i> , 2021 , 42, 673-676	4.4	7
539	Identification of dislocation-related and point-defects in III-As layers for silicon photonics applications. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 285101	3	2
538	CdTe solar cells: technology, operation and reliability. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 333003		5
537	Deep levels and carrier capture kinetics in n-GaAsBi alloys investigated by deep level transient spectroscopy. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 345109	3	2
536	Schottky Gate Induced Threshold Voltage Instabilities in p-GaN Gate AlGaIn/GaN HEMTs. <i>IEEE Transactions on Device and Materials Reliability</i> , 2021 , 21, 169-175	1.6	7
535	A new method for CdSexTe1-x band grading for high efficiency thin-absorber CdTe solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2021 , 226, 111081	6.4	6
534	. <i>IEEE Journal of Quantum Electronics</i> , 2021 , 57, 1-8	2	3
533	Preventing infectious diseases in Intensive Care Unit by medical devices remote control: Lessons from COVID-19. <i>Journal of Critical Care</i> , 2021 , 61, 119-124	4	5
532	. <i>IEEE Transactions on Instrumentation and Measurement</i> , 2021 , 70, 1-8	5.2	2
531	Degradation mechanisms of InGaIn visible LEDs and AlGaIn UV LEDs 2021 , 273-312		0
530	Cumulative Hot-Electron Trapping in GaN-Based Power HEMTs Observed by an Ultra-Fast (10V/ns) on-Wafer Methodology. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2021 , 1-1	5.6	1
529	Moisture resistance in perovskite solar cells attributed to a water-splitting layer. <i>Communications Materials</i> , 2021 , 2,	6	13
528	GaN-on-silicon transistors with reduced current collapse and improved blocking voltage by means of local substrate removal. <i>Applied Physics Express</i> , 2021 , 14, 036501	2.4	0

527	Gradual Degradation of InGaAs LEDs: Impact on Non-Radiative Lifetime and Extraction of Defect Characteristics. <i>Materials</i> , 2021 , 14,	3.5	3
526	Role Redistribution Model Explaining the Thermally Activated RON Stress/Recovery Transients in Carbon-Doped AlGaN/GaN Power MIS-HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 697-703	2.9	15
525	Opportunities from Doping of Non-Critical Metal Oxides in Last Generation Light-Conversion Devices. <i>Advanced Energy Materials</i> , 2021 , 11, 2101041	21.8	8
524	Glass-ceramic composites for high-power white-light-emitting diodes. <i>Ceramics International</i> , 2021 , 47, 17986-17992	5.1	0
523	Electric Field and Self-Heating Effects on the Emission Time of Iron Traps in GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 3325-3332	2.9	4
522	UV-Based Technologies for SARS-CoV2 Inactivation: Status and Perspectives. <i>Electronics (Switzerland)</i> , 2021 , 10, 1703	2.6	4
521	Short term reliability and robustness of ultra-thin barrier, 110 nm-gate AlN/GaN HEMTs. <i>Microelectronics Reliability</i> , 2021 , 123, 114199	1.2	1
520	Dynamic Performance Characterization Techniques in Gallium Nitride-Based Electronic Devices. <i>Crystals</i> , 2021 , 11, 1037	2.3	2
519	Modeling the electrical characteristics of InGaN/GaN LED structures based on experimentally-measured defect characteristics. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 425105	3	2
518	Effect of indium content and carrier distribution on the efficiency and reliability of InGaN/GaN-based multi quantum well light emitting diode. <i>Microelectronics Reliability</i> , 2021 , 126, 114377 ^{1,2}	1.2	0
517	Effects of quantum-well indium content on deep defects and reliability of InGaN/GaN light-emitting diodes with under layer. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 505108	3	0
516	TCAD modeling of bias temperature instabilities in SiC MOSFETs. <i>Solid-State Electronics</i> , 2021 , 185, 108067	6.7	1
515	Impact of thermal annealing on deep levels in nitrogen-implanted EGa ₂ O ₃ Schottky barrier diodes. <i>Journal of Applied Physics</i> , 2021 , 130, 245704	2.5	0
514	Use of Bilayer Gate Insulator in GaN-on-Si Vertical Trench MOSFETs: Impact on Performance and Reliability. <i>Materials</i> , 2020 , 13,	3.5	4
513	Exploration of gate trench module for vertical GaN devices. <i>Microelectronics Reliability</i> , 2020 , 114, 113828 ²	2.8	2
512	Non thermally-activated transients and buffer traps in GaN transistors with p-type gate: A new method for extracting the activation energy. <i>Microelectronics Reliability</i> , 2020 , 114, 113842	1.2	1
511	A novel on-wafer approach to test the stability of GaN-based devices in hard switching conditions: Study of hot-electron effects. <i>Microelectronics Reliability</i> , 2020 , 114, 113830	1.2	6
510	Degradation mechanism of 0.15 μ m AlGaN/GaN HEMTs: effects of hot electrons. <i>Microelectronics Reliability</i> , 2020 , 114, 113905	1.2	1

509	OFF-state trapping phenomena in GaN HEMTs: Interplay between gate trapping, acceptor ionization and positive charge redistribution. <i>Microelectronics Reliability</i> , 2020 , 114, 113841	1.2	3
508	Influence of CdTe solar cell properties on stability at high temperatures. <i>Microelectronics Reliability</i> , 2020 , 114, 113847	1.2	3
507	Reliability of H-terminated diamond MESFETs in high power dissipation operating condition. <i>Microelectronics Reliability</i> , 2020 , 114, 113898	1.2	0
506	Degradation of InGaN-based LEDs: Demonstration of a recombination-dependent defect-generation process. <i>Journal of Applied Physics</i> , 2020 , 127, 185701	2.5	9
505	Thermal droop in III-nitride based light-emitting diodes: Physical origin and perspectives. <i>Journal of Applied Physics</i> , 2020 , 127, 211102	2.5	18
504	BTI saturation and universal relaxation in SiC power MOSFETs. <i>Microelectronics Reliability</i> , 2020 , 109, 113642	1.2	1
503	Storage and release of buffer charge in GaN-on-Si HEMTs investigated by transient measurements. <i>Applied Physics Express</i> , 2020 , 13, 074003	2.4	5
502	. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 2765-2770	2.9	0
501	. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3978-3982	2.9	1
500	Modeling of gate capacitance of GaN-based trench-gate vertical metal-oxide-semiconductor devices. <i>Applied Physics Express</i> , 2020 , 13, 024006	2.4	2
499	COVID-19: ensuring our medical equipment can meet the challenge. <i>Expert Review of Medical Devices</i> , 2020 , 17, 483-489	3.5	9
498	2020 ,		1
497	Reliability Physics of GaN HEMT Microwave Devices: The Age of Scaling 2020 ,		1
496	Trap Dynamics Model Explaining the RON Stress/Recovery Behavior in Carbon-Doped Power AlGaIn/GaN MOS-HEMTs 2020 ,		7
495	Coupling halide perovskites with different materials: From doping to nanocomposites, beyond photovoltaics. <i>Progress in Materials Science</i> , 2020 , 110, 100639	42.2	27
494	Modeling of the Vertical Leakage Current in AlN/Si Heterojunctions for GaN Power Applications. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 595-599	2.9	5
493	Vertical Leakage in GaN-on-Si Stacks Investigated by a Buffer Decomposition Experiment. <i>Micromachines</i> , 2020 , 11,	3.3	1
492	Observation of ID-VD Kink in N-Polar GaN MIS-HEMTs at Cryogenic Temperatures. <i>IEEE Electron Device Letters</i> , 2020 , 41, 345-348	4.4	5

491	Understanding γ -Ray Induced Instability in AlGaIn/GaN HEMTs Using a Physics-Based Compact Model. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 1126-1131	2.9	6
490	Efficiency and Catastrophic Failure of High-Power Blue GaN LEDs During Extremely High Temperature and Current Stress. <i>IEEE Transactions on Device and Materials Reliability</i> , 2020 , 20, 429-435	1.6	3
489	Modeling the degradation mechanisms of AlGaIn-based UV-C LEDs: from injection efficiency to mid-gap state generation. <i>Photonics Research</i> , 2020 , 8, 1786	6	9
488	Analysis of threshold voltage instabilities in semi-vertical GaN-on-Si FETs. <i>Applied Physics Express</i> , 2020 , 13, 024004	2.4	8
487	Fast System to measure the dynamic on-resistance of on-wafer 600V normally off GaN HEMTs in hard-switching application conditions. <i>IET Power Electronics</i> , 2020 , 13, 2390-2397	2.2	7
486	Carrier capture kinetics, deep levels, and isolation properties of $\text{AlGaIn}/\text{Ga}_2\text{O}_3$ Schottky-barrier diodes damaged by nitrogen implantation. <i>Applied Physics Letters</i> , 2020 , 117, 262108	3.4	8
485	Degradation Mechanisms of GaN-Based Vertical Devices: A Review. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900750	1.6	3
484	Vertical breakdown of GaN on Si due to V-pits. <i>Journal of Applied Physics</i> , 2020 , 127, 015701	2.5	15
483	High Breakdown Voltage and Low Buffer Trapping in Superlattice GaN-on-Silicon Heterostructures for High Voltage Applications. <i>Materials</i> , 2020 , 13,	3.5	6
482	Cause and Effects of OFF-State Degradation in Hydrogen-Terminated Diamond MESFETs. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 4021-4026	2.9	2
481	GaN Vertical p-n Diodes in Avalanche Regime: Time-Dependent Behavior and Degradation. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1300-1303	4.4	2
480	Excitation Intensity and Temperature-Dependent Performance of InGaIn/GaN Multiple Quantum Wells Photodetectors. <i>Electronics (Switzerland)</i> , 2020 , 9, 1840	2.6	3
479	Highly stable threshold voltage in GaN nanowire FETs: The advantages of p-GaN channel/ Al_2O_3 gate insulator. <i>Applied Physics Letters</i> , 2020 , 117, 203501	3.4	5
478	GaN-based high-periodicity multiple quantum well solar cells: Degradation under optical and electrical stress. <i>Microelectronics Reliability</i> , 2020 , 114, 113802	1.2	2
477	2020 ,		2
476	Geometric Modeling of Thermal Resistance in GaN HEMTs on Silicon. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 5408-5414	2.9	2
475	. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3954-3959	2.9	12
474	Degradation mechanisms in high power InGaIn semiconductor lasers investigated by electrical, optical, spectral and C-DLTS measurements. <i>Microelectronics Reliability</i> , 2020 , 114, 113786	1.2	

473	Investigation of Current-Driven Degradation of 1.3 μm Quantum-Dot Lasers Epitaxially Grown on Silicon. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2020 , 26, 1-8	3.8	8
472	Low On-Resistance and Low Trapping Effects in 1200 V Superlattice GaN-on-Silicon Heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900687	1.6	5
471	High-Current Stress of UV-B (In)AlGaIn-Based LEDs: Defect-Generation and Diffusion Processes. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 3387-3392	2.9	13
470	Buffer breakdown in GaN-on-Si HEMTs: A comprehensive study based on a sequential growth experiment. <i>Microelectronics Reliability</i> , 2019 , 100-101, 113461	1.2	7
469	ESD-failure of E-mode GaN HEMTs: Role of device geometry and charge trapping. <i>Microelectronics Reliability</i> , 2019 , 100-101, 113334	1.2	5
468	Stability and degradation of isolation and surface in Ga ₂ O ₃ devices. <i>Microelectronics Reliability</i> , 2019 , 100-101, 113453	1.2	4
467	Stability and degradation of AlGaIn-based UV-B LEDs: Role of doping and semiconductor defects. <i>Microelectronics Reliability</i> , 2019 , 100-101, 113418	1.2	7
466	Gate Reliability of p-GaN Gate AlGaIn/GaN High Electron Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 379-382	4.4	16
465	Perimeter Driven Transport in the p-GaN Gate as a Limiting Factor for Gate Reliability 2019 ,		18
464	. <i>IEEE Journal of Quantum Electronics</i> , 2019 , 55, 1-7	2	12
463	Evidence of Spiro-OMeTAD De-doping by tert-Butylpyridine Additive in Hole-Transporting Layers for Perovskite Solar Cells. <i>Chem</i> , 2019 , 5, 1806-1817	16.2	54
462	NanoElectronics roadmap for Europe: From nanodevices and innovative materials to system integration. <i>Solid-State Electronics</i> , 2019 , 155, 7-19	1.7	12
461	Evidence for defect-assisted tunneling and recombination at extremely low current in InGaIn/GaN-based LEDs. <i>Applied Physics Express</i> , 2019 , 12, 052007	2.4	9
460	Demonstration of UV-Induced Threshold Voltage Instabilities in Vertical GaN Nanowire Array-Based Transistors. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 2119-2124	2.9	5
459	Positive temperature dependence of time-dependent breakdown of GaN-on-Si E-mode HEMTs under positive gate stress. <i>Applied Physics Letters</i> , 2019 , 115, 052103	3.4	19
458	2019 ,		4
457	Influence of Gate Length on pBTI in GaN-on-Si E-Mode MOSc-HEMT 2019 ,		4
456	Threshold Voltage Instability Mechanisms in p-GaN Gate AlGaIn/GaN HEMTs 2019 ,		17

455	Degradation processes of 280 nm high power DUV LEDs: impact on parasitic luminescence. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCC19	1.4	7
454	Reliability comparison of AlGaIn/GaN HEMTs with different carbon doping concentration. <i>Microelectronics Reliability</i> , 2019 , 100-101, 113489	1.2	3
453	Investigation into trapping modes and threshold instabilities of state-of-art commercial GaN HEMTs. <i>Microelectronics Reliability</i> , 2019 , 100-101, 113464	1.2	2
452	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4597-4603	2.9	8
451	Characterization of charge trapping mechanisms in GaN vertical Fin FETs under positive gate bias. <i>Microelectronics Reliability</i> , 2019 , 100-101, 113488	1.2	7
450	Linearity and robustness evaluation of 150-nm AlN/GaN HEMTs. <i>Microelectronics Reliability</i> , 2019 , 100-101, 113388	1.2	3
449	Reliability of Ultraviolet Light-Emitting Diodes. <i>Solid State Lighting Technology and Application Series</i> , 2019 , 397-424	0.7	2
448	Investigation of nBTI degradation on GaN-on-Si E-mode MOSc-HEMT 2019 ,		10
447	Special Issue on Reliability. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4497-4503	2.9	
446	A film-forming graphene/diketopyrrolopyrrole covalent hybrid with far-red optical features: Evidence of photo-stability. <i>Synthetic Metals</i> , 2019 , 258, 116201	3.6	5
445	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 337-342	2.9	13
444	Difluorochloromethane treated thin CdS buffer layers for improved CdTe solar cells. <i>Thin Solid Films</i> , 2019 , 672, 7-13	2.2	3
443	Analysis of magnesium zinc oxide layers for high efficiency CdTe devices. <i>Thin Solid Films</i> , 2019 , 672, 22-25	2.2	10
442	The Effect of Proton Irradiation in Suppressing Current Collapse in AlGaIn/GaN High-Electron-Mobility Transistors. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 372-377	2.9	10
441	Understanding lead iodide perovskite hysteresis and degradation causes by extensive electrical characterization. <i>Solar Energy Materials and Solar Cells</i> , 2019 , 189, 43-52	6.4	18
440	. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 1303-1307	2.9	6
439	The 2018 GaN power electronics roadmap. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 163001	3	527
438	Chip-Level Degradation of InGaIn-Based Optoelectronic Devices. <i>Solid State Lighting Technology and Application Series</i> , 2018 , 15-48	0.7	

437	Trapping phenomena and degradation mechanisms in GaN-based power HEMTs. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 118-126	4.3	53
436	Physical mechanisms limiting the performance and the reliability of GaN-based LEDs 2018 , 455-489		5
435	2018 ,		3
434	Review of dynamic effects and reliability of depletion and enhancement GaN HEMTs for power switching applications. <i>IET Power Electronics</i> , 2018 , 11, 668-674	2.2	19
433	GaN-Based Laser Wireless Power Transfer System. <i>Materials</i> , 2018 , 11,	3.5	13
432	Study and Development of a Fluorescence Based Sensor System for Monitoring Oxygen in Wine Production: The WOW Project. <i>Sensors</i> , 2018 , 18,	3.8	12
431	Observation of Hot Electron and Impact Ionization in N-Polar GaN MIS-HEMTs. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1007-1010	4.4	12
430	Impact of Substrate Resistivity on the Vertical Leakage, Breakdown, and Trapping in GaN-on-Si E-Mode HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2765-2770	2.9	21
429	. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2778-2783	2.9	31
428	Defect-generation and diffusion in (In)AlGaIn-based UV-B LEDs submitted to constant current stress 2018 ,		2
427	Positive and negative threshold voltage instabilities in GaN-based transistors. <i>Microelectronics Reliability</i> , 2018 , 80, 257-265	1.2	15
426	Impact of dislocations on DLTS spectra and degradation of InGaIn-based laser diodes. <i>Microelectronics Reliability</i> , 2018 , 88-90, 864-867	1.2	4
425	2018 ,		7
424	Power GaN HEMT degradation: from time-dependent breakdown to hot-electron effects 2018 ,		3
423	Analysis and Reliability Study of Luminescent Materials for White Lighting. <i>Proceedings (mdpi)</i> , 2018 , 2, 1158	0.3	1
422	Degradation of GaN-on-GaN vertical diodes submitted to high current stress. <i>Microelectronics Reliability</i> , 2018 , 88-90, 568-571	1.2	8
421	Failure limits and electro-optical characteristics of GaN-based LEDs under electrical overstress. <i>Microelectronics Reliability</i> , 2018 , 88-90, 887-890	1.2	2
420	Gate Conduction Mechanisms and Lifetime Modeling of p-Gate AlGaIn/GaN High-Electron-Mobility Transistors. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 5365-5372	2.9	40

419	Degradation of vertical GaN-on-GaN fin transistors: Step-stress and constant voltage experiments. <i>Microelectronics Reliability</i> , 2018 , 88-90, 620-626	1.2	5
418	On-wafer RF stress and trapping kinetics of Fe-doped AlGaIn/GaN HEMTs. <i>Microelectronics Reliability</i> , 2018 , 88-90, 397-401	1.2	1
417	Impact of the substrate and buffer design on the performance of GaN on Si power HEMTs. <i>Microelectronics Reliability</i> , 2018 , 88-90, 584-588	1.2	11
416	Current induced degradation study on state of the art DUV LEDs. <i>Microelectronics Reliability</i> , 2018 , 88-90, 868-872	1.2	14
415	Evaluation of novel carrier substrates for high reliability and integrated GaN devices in a 200 mm complementary metal-oxide semiconductor compatible process. <i>MRS Communications</i> , 2018 , 8, 1387-1397	2.7	2
414	Impact of sidewall etching on the dynamic performance of GaN-on-Si E-mode transistors. <i>Microelectronics Reliability</i> , 2018 , 88-90, 572-576	1.2	15
413	Degradation mechanisms of heterogeneous III-V/Silicon loop-mirror laser diodes for photonic integrated circuits. <i>Microelectronics Reliability</i> , 2018 , 88-90, 855-858	1.2	5
412	Evidence of optically induced degradation in gallium nitride optoelectronic devices. <i>Applied Physics Express</i> , 2018 , 11, 111002	2.4	6
411	Reliability of Blue-Emitting Eu-Doped Phosphors for Laser-Lighting Applications. <i>Materials</i> , 2018 , 11,	3.5	1
410	Reliability of GaN-Based Power Devices. <i>Integrated Circuits and Systems</i> , 2018 , 75-99	0.2	
409	2018 ,		6
408	On the origin of the leakage current in p-gate AlGaIn/GaN HEMTs 2018 ,		22
407	. <i>IEEE Transactions on Device and Materials Reliability</i> , 2018 , 18, 391-396	1.6	12
406	. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 1032-1037	2.9	2
405	Smart Power Devices Nanotechnology 2017 , 163-204		2
404	Potential induced degradation of N-type bifacial silicon solar cells: An investigation based on electrical and optical measurements. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 168, 51-61	6.4	26
403	. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 73-77	2.9	13
402	2017 ,		32

401	Electrical Properties, Reliability Issues, and ESD Robustness of InGaN-Based LEDs. <i>Topics in Applied Physics</i> , 2017 , 363-395	0.5	1
400	. <i>IEEE Journal of Quantum Electronics</i> , 2017 , 53, 1-8	2	9
399	Characterization of Defects in AlGaIn/GaN HEMTs Based on Nonlinear Microwave Current Transient Spectroscopy. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 2135-2141	2.9	8
398	Defect generation in deep-UV AlGaIn-based LEDs investigated by electrical and spectroscopic characterisation 2017 ,		3
397	On recoverable behavior of PBTI in AlGaIn/GaN MOS-HEMT. <i>Solid-State Electronics</i> , 2017 , 132, 49-56	1.7	20
396	. <i>IEEE Transactions on Device and Materials Reliability</i> , 2017 , 17, 191-196	1.6	5
395	. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 200-205	2.9	41
394	Evidence of Hot-Electron Effects During Hard Switching of AlGaIn/GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3734-3739	2.9	53
393	Long-term degradation of InGaN-based laser diodes: Role of defects. <i>Microelectronics Reliability</i> , 2017 , 76-77, 584-587	1.2	1
392	Field- and current-driven degradation of GaN-based power HEMTs with p-GaN gate: Dependence on Mg-doping level. <i>Microelectronics Reliability</i> , 2017 , 76-77, 298-303	1.2	22
391	. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3616-3621	2.9	30
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12	Improvement of DC, low frequency and reliability properties of InAlAs/InGaAs InP-based HEMTs by means of an InP etch stop layer		14
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